

ELECTRICAL CHARACTERISTICS: OM200L120CMD (Tc= 25°C unless otherwise specified)

Characteristic	Symbol	Min.	Typ.	Max	Unit
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OFF CHARACTERISTICS

Collector Emitter Breakdown Voltage, VCE=0V	V _{CES}	1200			V
Zero Gate Voltage Drain Current, V _{GE} =0, V _{CE} =1200V	I _{CES}		2		μA
Gate Emitter Leakage Current, V _{GE} =+/-20V, V _{CE} =0V	I _{GES}		100		μA

ON CHARACTERISTICS

Gate Threshold Voltage, V _{CE} =V _{GE} , I _C =6mA	V _{GE(TH)}	4.5	5.5	6.5	V
Collector Emitter Saturation Voltage, V _{GE} =15V, I _C =200A	V _{CE(SAT)}			2.6	V

DYNAMIC CHARACTERISTICS

Fwd. Transconductance	V _{CE} =5V, I _C =200A	g _{fs}	17		S
Input Capacitance	V _{GE} =0	C _{ies}		17	nF
Output Capacitance	V _{CE} =25V	C _{oes}		3	nF
Rev. Transfer Capacitance	f=1.0MHz	C _{res}		1.5	nF

SWITCHING INDUCTIVE LOAD CHARACTERISTICS

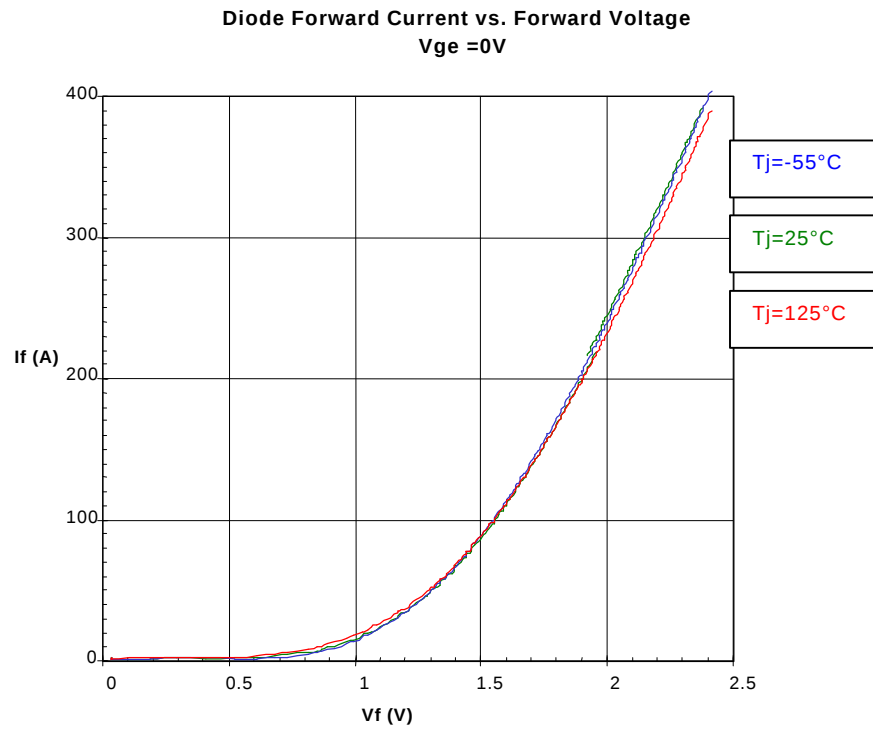
Turn-On Delay Time	V _{CC} = 600V, I _C =200A V _{GE} =+15/-10V, R _G =5.1Ω L=100μH	t _(on)		400	nS
Rise Time		t _r	300		nS
Turn-on Losses		E _{on}			mJ
Turn-off Delay Time		t _{d(off)}	700		nS
Fall Time		t _f	250		nS
Turn-off Losses		E _{off}			mJ

DIODE CHARACTERISTICS

Maximum Forward Voltage	I _F =200A, T _j =25°C T _j =125°C	V _F	2.0	2.8	V
Reverse Recovery Characteristics	V _R =600V, T _j =25°C I _F =200A, T _j =125°C dI/dt=-1500A/μS T _j =25°C T _j =125°C T _j =25°C T _j =125°C	Q _{rr}	10		μC
			15		
		I _{rr}	75		A
			95		
		t _{rr}	100		nS
			150		

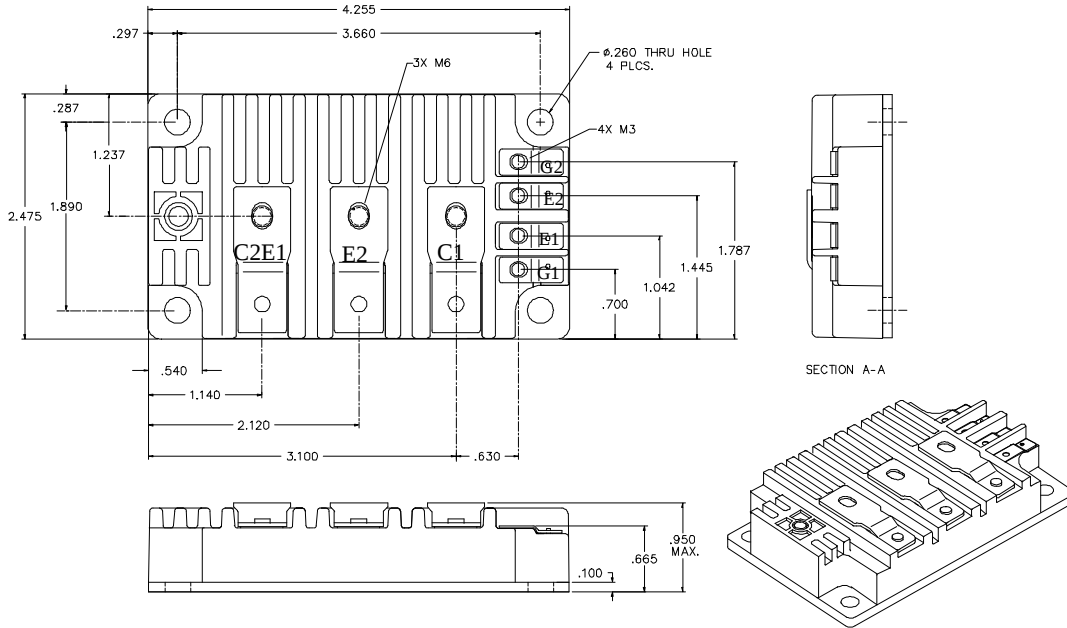
THERMAL AND MECHANICAL CHARACTERISTICS

Thermal Resistance, Junction to Case (Per IGBT)	R _{thJC}			0.07	°C/W
Thermal Resistance, Junction to Case (Per Diode)	R _{thJC}			0.12	°C/W
Maximum Junction Temperature	T _{JMAX}			150	°C
Isolation Voltage	V _{IS} _{RMS}			2500	V
Screw Torque	Mounting	-	15	20	in-lb
Screw Torque (M6)	Terminals		10	12	in-lb
Screw Torque (M3)	Terminals	-	6	8	in-lb
Module Weight	-		320		Grams

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MECHANICAL OUTLINE



EQUIVALENT CIRCUIT

